

## **Martino Lorenzini - CV**

Martino Lorenzini received the Laurea (cum laude) and Ph.D. degrees in electronic engineering from the University of Bologna, Bologna, Italy, in 1993 and 1997, respectively. In 2001, he received a M. Sc. degree in physics from the Katholieke Universiteit Leuven, Leuven, Belgium. From 1994 to 1997, he was with the Department of Electronics, Computer Science and Systems (DEIS) of the University of Bologna, where he carried out his research activity in the field of semiconductor-device modeling and simulation. In 1998, he joined the Interuniversity Microelectronics Center (IMEC) in Leuven, Belgium, where he worked on several research topics in the field of floating-gate as well as nitride-based non-volatile memory devices. In 2005, he joined Philips Semiconductors, Nijmegen, The Netherlands, initially involved in the development of RF power LDMOS devices. Since 2008, he has been working on the development of AlGaIn/GaN HEMTs for RF and microwave applications in cooperation with external foundries and research partners. Currently, he is with Gallium Semiconductor Netherlands. He has authored or coauthored more than 40 journal and conference papers. His research interests include the physics and modeling of semiconductor devices, with present emphasis on high-power and high-frequency HEMTs.